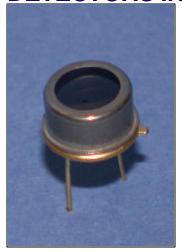
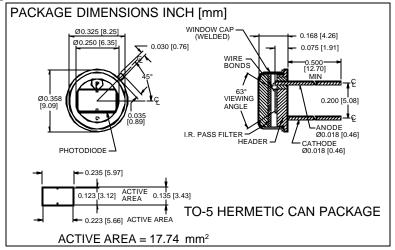
## **PHOTONIC** DETECTORS INC.

### Silicon Photodiode, Near I.R. Photoconductive Type PDI-C114-F





### **FEATURES**

- High speed
- Match to I.R. emitters
- Hermetic package

### **DESCRIPTION**

The PDI-C114-F is a silicon, PIN planar • I.R. pass visible rejection diffused photodiode with NIR pass, visible light rejection optical filter. Ideal for high speed, low capacitance, photoconductive NIR applications. Packaged in a hermetic

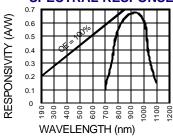
# TO-5 metal can with a flat window cap. ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

| SYMBOL           | PARAMETER                   | MIN | MAX  | UNITS |
|------------------|-----------------------------|-----|------|-------|
| V <sub>BR</sub>  | Reverse Voltage             |     | 100  | V     |
| T <sub>stg</sub> | Storage Temperature         | -55 | +100 | °C    |
| То               | Operating Temperature Range | -40 | +80  | °C    |
| Ts               | Soldering Temperature*      |     | +240 | °C    |
| I <sub>L</sub>   | Light Current               |     | 0.5  | mA    |

### **APPLICATIONS**

- I.R. detector
- I.R. laser detector
- Photo-interrupters
- Industrial controls

### SPECTRAL RESPONSE



### **ELECTRO-OPTICAL CHARACTERISTICS** (TA=25°C unless otherwise noted)

| SYMBOL          | CHARACTERISTIC             | TEST CONDITIONS                | MIN | TYP                   | MAX  | UNITS   |
|-----------------|----------------------------|--------------------------------|-----|-----------------------|------|---------|
| lsc             | Short Circuit Current      | H = 100 fc, 2850 K             | 171 | 212                   |      | mA      |
| ΙD              | Dark Current               | $H = 0, V_R = 10 V$            |     | 3                     | 8.0  | nA      |
| Rsh             | Shunt Resistance           | $H = 0, V_{R} = 10 \text{ mV}$ | 150 | 500                   |      | MΩ      |
| TC Rsh          | RSH Temp. Coefficient      | $H = 0, V_{R} = 10 \text{ mV}$ |     | -8                    |      | %/℃     |
| CJ              | Junction Capacitance       | $H = 0, V_R = 10 V^{**}$       |     | 50                    |      | pF      |
| λrange          | Spectral Application Range | Spot Scan                      | 700 |                       | 1100 | nm      |
| λр              | Spectral Response - Peak   | Spot Scan                      |     | 950                   |      | nm      |
| V <sub>BR</sub> | Breakdown Voltage          | I = 10 <b>m</b> A              | 100 | 125                   |      | V       |
| N EP            | Noise Equivalent Power     | V <sub>R</sub> = 10 V @ Peak   |     | 5.0x10 <sup>-14</sup> |      | W/ √ Hz |
| tr              | Response Time              | $RL = 1 K\Omega V_R = 50 V$    |     | 20                    |      | nS      |

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. \*\* f = 1 MHz